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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>				<b>Complete if Known</b>	
Sheet	1	of	2	Application Number	10/797,231
				Filing Date	March 10, 2004
				First Named Inventor	Matthew T. Currie
				Art Unit	2812
				Examiner Name	A. G. Ghyka
				Attorney Docket Number	ASC-057C1

<b>U.S. PATENT DOCUMENTS</b>					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
A70*	US-5,166,084		11-24-1992	Pfiester	
A71*	US-5,212,110		05-18-1993	Pfiester et al.	
A72*	US-5,981,400		11-09-1999	Lo	
A73*	US-6,074,919		06-13-2000	Gardner et al.	
A74*	US-6,103,559		08-15-2000	Gardner et al.	
A75*	US-6,154,475		11-28-2000	Soref et al.	
A76*	US-6,162,688		12-19-2000	Gardner et al.	
A77*	US-6,191,432		02-20-2001	Sugiyama et al.	
A78*	US-6,194,722		02-27-2001	Fiorini et al.	
A79*	US-6,210,988		04-03-2001	Howe et al.	
A80*	US-6,218,677		04-17-2001	Broekaert	
A81*	US-6,583,015-A1		06-24-2003	Fitzgerald et al.	
A82*	US-6,846,715		01-25-2005	Fitzgerald et al.	
A83*	US-7,217,668		05-15-2007	Fitzgerald et al.	
A84*	US-20050003229		01-06-2005	Bedell et al.	
A85*	US-20070082470		04-12-2007	Fitzgerald et al.	

<b>FOREIGN PATENT DOCUMENTS</b>					
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)			
	B1	EP-0 587 520	03-16-1994		<input checked="" type="checkbox"/>
	B2	JP-2000-031491	01-28-2000		<input checked="" type="checkbox"/>

Examiner Signature	Date Considered
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. \*CITE NO.: Those application(s) which are marked with an single asterisk (\*) next to the Cite No. are not supplied (under 37 CFR 1.98(a)(2)(iii)) because that application was filed after June 30, 2003 or is available in the IFW. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449/PTO				<b><i>Complete if Known</i></b>	
				Application Number	10/797,231
				Filing Date	March 10, 2004
				First Named Inventor	Richard Hammond
				Art Unit	2812
				Examiner Name	A. G. Ghyka
Sheet	2	of	2	Attorney Docket Number	ASC-057C1

<b>NON PATENT LITERATURE DOCUMENTS</b>			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	C86	Abramo, A. et al., "Mobility Simulation of a Novel Si/SiGe FET Structure," IEEE Electron Device Letters, vol. 17, no. 2, February 1996, pp. 59-61.	
	C87	Hellberg, P.E. et al., "Oxidation of silicon-germanium alloys. I. An experimental study," Journal of Applied Physics, vol. 82, no. 11, December 1, 1997, pp. 5773-5778.	
	C88	International Search Report for Patent Application No. PCT/US 01/24614, dated 3/11/2002, 3 pages.	
	C89	Notice of Assignment of Inter Partes Reexamination Request, Patent No. 6,846,715, July 27, 2006.	
	C90	Office Action in Inter Partes Reexamination, Patent No. 6,846,715, August 30, 2006.	
	C91	Niino, T. et al., "SiGe Passivation for Si MBE Regrowth," Japanese Journal of Applied Physics, vol. 29, no. 9, pp. 1702-1704, September 1990.	
	C92	O'Neill, A.G. et al., "Deep Submicron CMOS Based on Silicon Germanium Technology," IEEE Transactions on Electron Devices, vol. 43, no. 6, June 1996, pp. 911-918.	
	C93	Order Granting/Denying Request for Inter Partes Reexamination, Patent No. 6,846,715, August 30, 2006.	
	C94	Request for Inter Partes Reexamination of U.S. Patent No. 6,846,715, June 26, 2006.	
	C95	Wolf, "Silicon Processing for the VLSI Era, vol. 2: Process Integration," pp. 27, 331 (Lattice Press, 1990).	
	C96	Wu et al., "High-Quality Thermal Oxide Grown on High-Temperature-Formed SiGe," 147 J. Electrochemical Soc'y 5, pp. 1962-64 (2000).	

Examiner Signature	Date Considered
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